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State	Finished
Completed on	Thursday, 4 August 2022, 6:01 PM
Time taken	2 hours 25 mins
Grade	94.0 out of 106.0 (89%)

Question **1**

Correct

Mark 2.0 out of 2.0

Which of the following is true ?

Select one:

- ☐ a. Boron has 3 electrons in its outermost shell
- ☐ b. Silicon has 4 electrons in its outermost shell
- ☒ c. All of these
- ☐ d. Arsenic has 5 electrons in its outermost shell
- ☐ e. Phosphorus has 5 electrons in its outermost shell



The correct answer is: All of these

Correct

Marks for this submission: 2.0/2.0.

Question **2**

Correct

Mark 2.0 out of 2.0

Which of the following is true ?

Select one:

- ☐ a. All of these
- ☐ b. In intrinsic Silicon at 300°K there are no free electrons
- ☐ c. In intrinsic Silicon at 300°K only free electrons can conduct electricity
- ☒ d. In intrinsic Silicon at 300°K the number of holes is far less than the number of Silicon atoms
- ☐ e. In intrinsic Silicon at 300°K the number of free electrons is about equal to the number of Silicon atoms



The correct answer is: In intrinsic Silicon at 300°K the number of holes is far less than the number of Silicon atoms

Correct

Marks for this submission: 2.0/2.0.

Question **3**

Correct

Mark 2.0 out of 2.0

As the reverse bias voltage across a PN junction is decreased, the potential barrier will

Select one:

- ☒ a. Decrease
- ☐ b. None of these
- ☐ c. Stays the same
- ☐ d. Increase
- ☐ e. No way to determine



The correct answer is: Decrease

Correct

Marks for this submission: 2.0/2.0.

Question **4**

Correct

Mark 2.0 out of 2.0

Which of the following is true for the depletion region surrounding a PN junction?

Select one:

- ☐ a. None of these
- ☐ b. In the depletion region there are free electrons and holes which cause a separation of charge
- ☐ c. In the depletion region there are almost no immobile ions
- ☒ d. In the depletion region the amount of charge stored varies with the applied bias, causing a capacitance
- ☐ e. In the depletion region there is zero electric field



The correct answer is: In the depletion region the amount of charge stored varies with the applied bias, causing a capacitance

Correct

Marks for this submission: 2.0/2.0.

Question **5**

Correct

Mark 2.0 out of 2.0

Which of the following circuits is part of a typical DC power supply?

Select one:

- ☒ a. None of these
- ☐ b. A diode limiter
- ☐ c. A current regulator
- ☐ d. A high pass filter
- ☐ e. A load resistor



The correct answer is: None of these

Correct

Marks for this submission: 2.0/2.0.

Question **6**

Correct

Mark 2.0 out of 2.0

When does the voltage across a diode depend exponentially on the current flowing through?

Select one:

- ☐ a. When the voltage on the P side is higher than the voltage on the N side by at least 500mV
- ☐ b. When the voltage on the P side is higher than the voltage on the N side
- ☐ c. When the voltage on the N side is higher than the voltage on the P side, but lower than the breakdown voltage
- ☐ d. When the voltage on the N side is higher than the voltage on the P side, and higher than the breakdown voltage
- ☒ e. None of these



The correct answer is: None of these

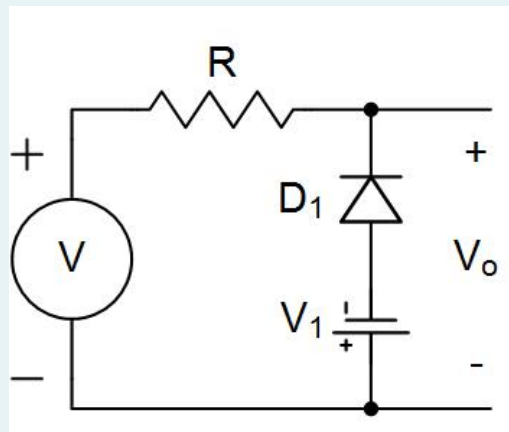
Correct

Marks for this submission: 2.0/2.0.

Question 7

Correct

Mark 2.0 out of 2.0



Assuming ideal diodes, for the diode circuit shown :

Select one:

- ☐ a. The gain is equal to 0 when V is $> -V_1$
- ☐ b. The minimum output voltage is $+V_1$
- ☐ c. None of these
- ☒ d. The gain is equal to 0 when V is $< -V_1$
- ☐ e. The maximum output voltage is $+V_1$



The correct answer is: The gain is equal to 0 when V is $< -V_1$

Correct

Marks for this submission: 2.0/2.0.

Question 8

Correct

Mark 2.0 out of 2.0

Which of the following would cause the ripple voltage at the output of a power supply to increase?

Select one:

- ☐ a. Increasing the size of the load resistance
- ☐ b. Increasing the size of the filter capacitor
- ☒ c. None of these
- ☐ d. Reducing the amplitude of the input voltage
- ☐ e. Increasing the frequency of the input voltage



The correct answer is: None of these

Correct

Marks for this submission: 2.0/2.0.

Question 9

Correct

Mark 2.0 out of 2.0

Compared to the process transconductance for a PMOS FET, the process transconductance for an NMOS FET is :

Select one:

- ☐ a. Same
- ☐ b. None of these
- ☒ c. Larger
- ☐ d. Smaller
- ☐ e. Impossible to determine



The correct answer is: Larger

Correct

Marks for this submission: 2.0/2.0.

Question 10

Correct

Mark 2.0 out of 2.0

If an NMOS FET is biased with $V_{gs} \ll V_t$ and $V_{ds} < V_{gs} - V_t$, the device is in :

Select one:

- ☐ a. None of these
- ☐ b. Sub-threshold
- ☐ c. Triode
- ☐ d. Saturation
- ☒ e. Cutoff



The correct answer is: Cutoff

Correct

Marks for this submission: 2.0/2.0.

Question **11**

Correct

Mark 2.0 out of 2.0

Silicon has approximately 1.5×10^{10} atoms/cm³.

Select one:

- ☐ True
- ☒ False ✓

The correct answer is 'False'.

Correct

Marks for this submission: 2.0/2.0.

Question **12**

Correct

Mark 2.0 out of 2.0

At room temperature (300°K) there is enough thermal energy to break some bonds and create electron-hole pairs.

Select one:

- ☒ True ✓
- ☐ False

The correct answer is 'True'.

Correct

Marks for this submission: 2.0/2.0.

Question **13**

Correct

Mark 2.0 out of 2.0

The ionized atoms in the depletion region cause a separation of charge between the two sides of a PN junction, with positive charge on the p-side and negative charge on the n-side.

Select one:

- ☐ True
- ☒ False ✓

The correct answer is 'False'.

Correct

Marks for this submission: 2.0/2.0.

Question **14**

Correct

Mark 2.0 out of 2.0

The Zener effect typically causes the reverse breakdown of PN junctions which break down at voltages $< 5V$.

Select one:

- ☒ True ✓
- ☐ False

The correct answer is 'True'.

Correct

Marks for this submission: 2.0/2.0.

Question **15**

Correct

Mark 2.0 out of 2.0

The RC time constant for the filter capacitor in a power supply is typically set much smaller than the period of the input sine wave.

Select one:

- ☐ True
- ☒ False ✓

The correct answer is 'False'.

Correct

Marks for this submission: 2.0/2.0.

Question **16**

Correct

Mark 2.0 out of 2.0

Bridge rectifiers are often used in power supplies instead of center-tapped transformers to lower cost.

Select one:

- ☒ True ✓
- ☐ False

The correct answer is 'True'.

Correct

Marks for this submission: 2.0/2.0.

Question **17**

Correct

Mark 2.0 out of 2.0

Diodes can be used to limit how low the magnitude of a signal can go.

Select one:

- ☐ True
- ☒ False ✓

The correct answer is 'False'.

Correct

Marks for this submission: 2.0/2.0.

Question **18**

Correct

Mark 2.0 out of 2.0

For a Half Wave Rectifier the diode must be able to handle a Peak Inverse Voltage equal to nearly twice the peak of the input voltage.

Select one:

- ☐ True
- ☒ False ✓

The correct answer is 'False'.

Correct

Marks for this submission: 2.0/2.0.

Question **19**

Correct

Mark 2.0 out of 2.0

The flow of current between the drain and source of a MOSFET is controlled using electric fields.

Select one:

- ☒ True ✓
- ☐ False

The correct answer is 'True'.

Correct

Marks for this submission: 2.0/2.0.

Question **20**

Correct

Mark 2.0 out of 2.0

For a MOSFET in saturation, changes in V_{ds} have only a small effect on the drain current because the channel stops being pinched off at the drain end as $|V_{ds}|$ is increased.

Select one:

- ☐ True
- ☒ False ✓

The correct answer is 'False'.

Correct

Marks for this submission: 2.0/2.0.

Question **21**

Correct

Mark 6.0 out of 6.0

If a silicon diffusion is doped with phosphorus at a concentration of $8.7 \times 10^{16}/\text{cm}^3$, what is the concentration of holes in this piece of silicon per cm^3 ? Assume $n_i = 1.5 \times 10^{10}/\text{cm}^3$ at 300°K

Answer: ✓

The correct answer is: 2586

Correct

Marks for this submission: 6.0/6.0.

Question **22**

Correct

Mark 6.0 out of 6.0

If a PN junction is doped with boron at a concentration of $7.0 \times 10^{18}/\text{cm}^3$ and phosphorus at a concentration of $1.1 \times 10^{17}/\text{cm}^3$, then what is the built-in voltage in millivolts for this junction? Assume $n_i = 1.5 \times 10^{10}/\text{cm}^3$ and $V_t = kT/q = 26\text{mV}$ at 300°K . Since small changes in the built-in voltage imply large changes in the doping levels, be sure to give your answer to the nearest millivolt!

Answer: ✓

The correct answer is: 930

Correct

Marks for this submission: 6.0/6.0.

Question **23**

Correct

Mark 6.0 out of 6.0

If the DC bias voltage, V_d , across a forward biased PN junction is equal to 728 mV then what is the current flowing through this diode, I_d , in milliamps? Assume that the saturation current for the diode, I_s , is equal to 51 fA. (Note that 1 fA = 1 femtoamp = 1×10^{-15} A.) Also assume that the thermal voltage is equal to $V_t = kt/q = 26\text{mV}$. Since the diode current is very sensitive to small changes in the diode voltage, be sure to use V_d to the nearest millivolt when calculating your answer!

Answer: ✓

The correct answer is: 73.76

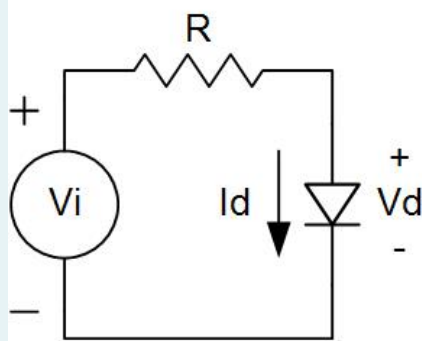
Correct

Marks for this submission: 6.0/6.0.

Question **24**

Correct

Mark 3.0 out of 6.0



If the input voltage to the diode circuit shown, V_i , changes by 1.9V then what will be the change in the diode voltage, V_d , in millivolts? To find the bias point needed for your small signal analysis use the constant voltage model for the diode with $V_d = 666\text{mV}$. Use a nominal value for V_i (the value before any changes) equal to 8.3V. Also use $R = 7.8\text{k}\Omega$ and $V_t = kt/q = 26\text{mV}$.

Answer: ✓

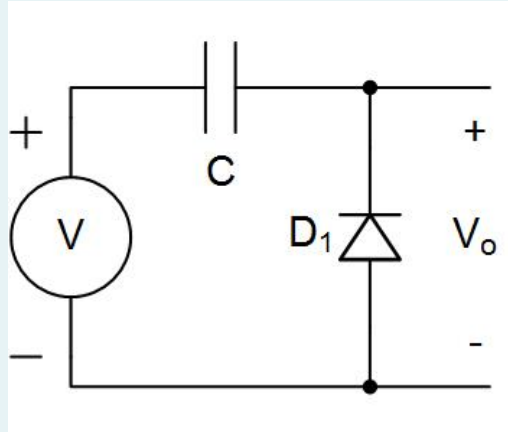
The correct answer is: 6.4

CorrectMarks for this submission: 6.0/6.0. Accounting for previous tries, this gives **3.0/6.0**.

Question 25

Correct

Mark 3.0 out of 6.0



For the diode circuit shown, what will the minimum output voltage, V_o , be in volts if the input voltage, V , is a square wave which varies between +1.8V and -9.2V ? Assume that when the diode is turned on the voltage across it will be 0.7V.

Answer: ✓

The correct answer is: -0.7

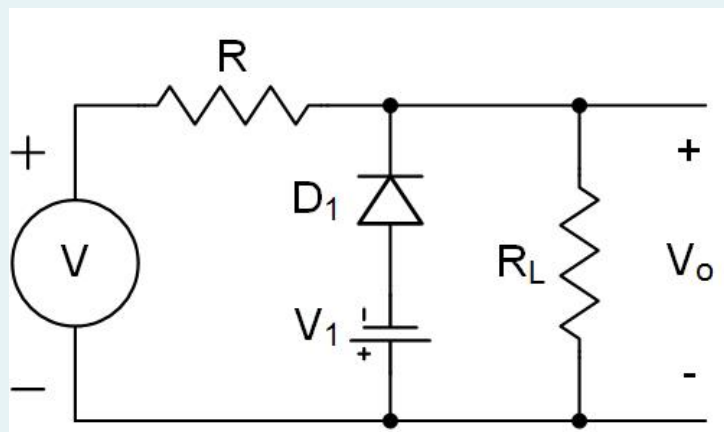
Correct

Marks for this submission: 6.0/6.0. Accounting for previous tries, this gives **3.0/6.0**.

Question 26

Correct

Mark 3.0 out of 6.0



For the diode circuit shown, what will the output voltage, V_o , be in volts if the input voltage, V , is equal to 6V ? Assume that when the diode is turned on the voltage across it will be 0.7V, and for the battery use $V_1 = 7.2V$. Also use $R = 4.5k\Omega$ and $R_L = 13.8k\Omega$.

Answer: 4.52 ✓

The correct answer is: 4.52

Correct

Marks for this submission: 6.0/6.0. Accounting for previous tries, this gives 3.0/6.0.

Question 27

Correct

Mark 3.0 out of 6.0

A full-wave diode rectifier circuit is driven by a 60Hz sine wave with a peak value of 11V. If the load resistance this circuit drives is $2.0k\Omega$ and the ripple voltage at the output is 0.23 Vpeak-to-peak, then what is the peak current in the diode in milliamps?

Answer: 174.49 ✓

The correct answer is: 174.5

Correct

Marks for this submission: 6.0/6.0. Accounting for previous tries, this gives 3.0/6.0.

Question **28**

Correct

Mark 6.0 out of 6.0

If a MOSFET with $W = 1.1 \mu\text{m}$ and $L = 0.5 \mu\text{m}$ is biased in triode, what is the gate-to-source capacitance, C_{gs} , in femtofarads? Assume the gate dielectric is silicon dioxide with $t_{ox} = 68.7 \text{ \AA}$.

Answer: ✓

The correct answer is: 1.4

Correct

Marks for this submission: 6.0/6.0.

Question **29**

Correct

Mark 6.0 out of 6.0

If an NMOS FET with $W = 68.9 \mu\text{m}$ and $L = 0.8 \mu\text{m}$ is biased in triode with $V_{gs} = 0.9$ and $V_{ds} = 0\text{V}$, what is the on-resistance of this MOS switch in Ohms? Use: $V_{TN} = 0.5\text{V}$, $k'_n = 100 \mu\text{A/V}^2$

Answer: ✓

The correct answer is: 290.3

Correct

Marks for this submission: 6.0/6.0.

Question **30**

Correct

Mark 6.0 out of 6.0

If a NMOS FET with $W/L = 24.7$ has $V_{gs} = 0.62$ and $V_{ds} = 0.84$, what is the drain current in microamps? Use: $V_{TN} = 0.5\text{V}$, $k'_n = 100 \mu\text{A/V}^2$, $\lambda = 0$

Answer: ✓

The correct answer is: 17.8

Correct

Marks for this submission: 6.0/6.0.

Question **31**

Correct

Mark 6.0 out of 6.0

A half-wave diode rectifier circuit is driven by a 60Hz sine wave with a peak value of 17V. If the load resistance this circuit drives is $8.0\text{k}\Omega$ and the ripple voltage at the output is 0.28 V_{peak-to-peak}, then during what percent of each cycle does the diode conduct?

Answer: ✓

The correct answer is: 2.89

Correct

Marks for this submission: 6.0/6.0.

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